

## P-Channel 30-V (D-S) MOSFET

### **Description**

The MS34P01 utilized advanced processing techniques to achieve the lowest possible on-resistance, extremely efficient and cost-effectiveness device. The device is universally preferred for all commercial-industrial surface mount applications and suited for low voltage applications such as DC/DC converters.

The device meets the RoHS and Green Product requirement with full function reliability approved.

#### **Features**

- Super High Dense Cell Design for Extremely Low R<sub>DS(ON)</sub>
- Low Gate Charge
- Green Device Available

#### **Typical Applications**

- Battery Protection
- Load Switch
- Hand-held Instrument

Package type: SOT-23

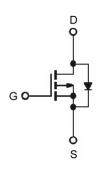
#### **Packing & Order Information**

3,000/Reel

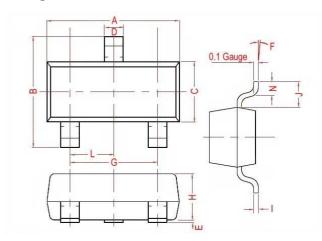


RoHS Compliant

#### **Graphic Symbol**

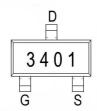


### **Package Dimension**



REF.	Millimeter		REF.	Millimeter		
	Min.	Max.	KEF.	Min.	Max.	
Α	2.70	3.10	G	1.90 Ref.		
В	2.30	3.00	Н	0.90	1.30	
С	1.20	1.75	I	0.05	0.21	
D	0.30	0.50	J	0.58 Ref.		
Е	0.01	0.15	L	0.95 Typ.		
F	0°	10°	N	0.20 Min.		

#### Marking





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### **MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS**

Absolute Maximum Ratings (unless otherwise specified)						
Symbol	Parameter	Value	Units			
$V_{DS}$	Drain-Source Voltage	-30	V			
V <sub>GS</sub>	Gate-Source Voltage	±12	V			
1	Continuous Drain Current <sup>3</sup> (T <sub>A</sub> =25°C)	-4.2	А			
I <sub>D</sub>	Continuous Drain Current <sup>3</sup> (T <sub>A</sub> =70°C)	-3.5	A			
I <sub>DM</sub>	Pulsed Drain Current <sup>1,2</sup> (T <sub>A</sub> =25°C)	-20	А			
P <sub>D</sub>	Power Dissipation (T <sub>A</sub> =25°C)	1.38	W			
T <sub>J</sub> /T <sub>STG</sub>	Operating Junction and Storage Temperature	-55 to +150	°C			

Thermal Resistance Ratings						
Symbol	Parameter	Maximum	Units			
$R_{\theta JA}$	Maximum Junction-to-Ambient <sup>3</sup>	90	°C/W			

Electrical Characteristics(T」=25°C unless otherwise specified)						
Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Units
$V_{GS\ (th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = -250 \mu A$	-0.5	-	-1.3	V
$BV_{DSS}$	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =-250μA	-30	-	-	V
<b>g</b> fs	Forward Transconductance	V <sub>DS</sub> =-5V, I <sub>D</sub> =-3A	-	9	-	S
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>DS</sub> =0V, V <sub>GS</sub> =±12V	-	-	±100	nA
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =-24V, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C	-	-	-1	μΑ
		V <sub>DS</sub> =-24V, V <sub>GS</sub> =0V, T <sub>J</sub> =55°C			-5	
R <sub>DS (on)</sub>	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =-10V, I <sub>D</sub> =-4.2A	-	-	53	
		$V_{GS} = -4.5V, I_{D} = -4.0A$	-	-	65	mΩ
		V <sub>GS</sub> =-2.5V, I <sub>D</sub> =-1.0A	-	-	120	
$V_{\text{SD}}$	Diode Forward Voltage <sup>2</sup>	I <sub>S</sub> =-1.2A, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C	-	-	-1.0	V
Is	Continuous Source Current (Diode)	V V OV Force Comment	-	-	-4.2	^
I <sub>SM</sub>	Pulsed Source Current (Diode)	V <sub>G</sub> =V <sub>D</sub> =0V, Force Current	-	-	-8.4	A

#### **Notes**

- 1. Pulsed width limited by maximum junction temperature.
- 2. The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%.
- 3. Surface mounted on 1 in 2 copper pad of FR4 board;  $270\,^{\circ}$ C/W when mounted on min. copper pad.



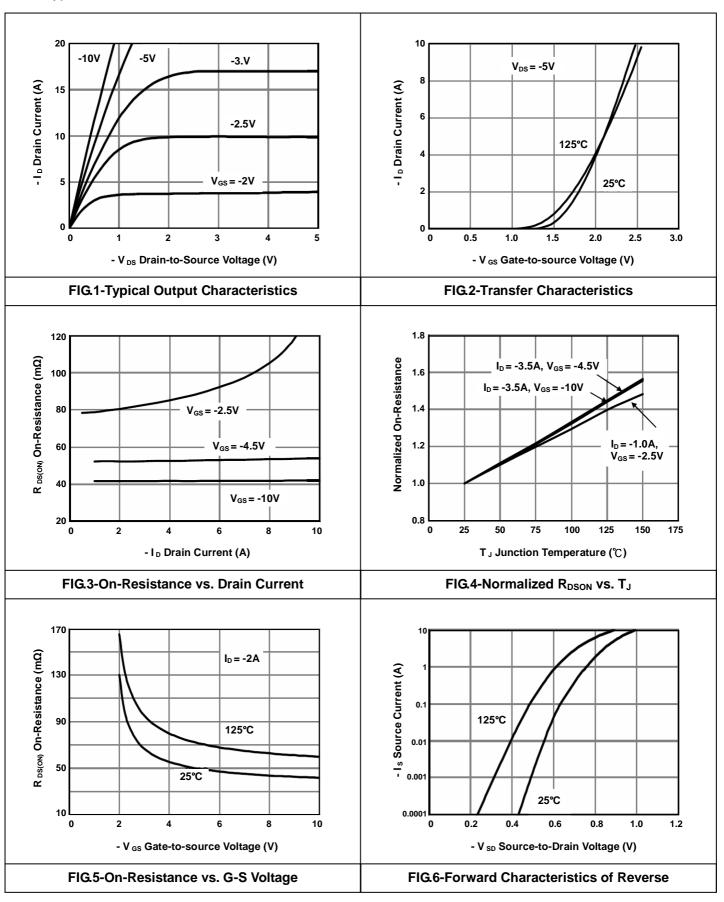
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Dynamic and switching Characteristics						
Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Units
Qg	Total Gate Charge <sup>2</sup>	V <sub>DS</sub> =-15V		9.4		
Q <sub>gs</sub>	Gate-Source Charge	I <sub>D</sub> =-4A		2		nC
Q <sub>gd</sub>	Gate-Drain Charge	V <sub>GS</sub> =-4.5V		3		
t <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DS</sub> =-15V		6.3		
t <sub>r</sub>	Rise Time	V <sub>GS</sub> =-10V		3.2		
t <sub>d(off)</sub>	Turn-Off Delay Time	$R_G = 6.0\Omega$		38.2		ns
t <sub>f</sub>	Fall Time	R <sub>L</sub> =3.6Ω		12		
C <sub>ISS</sub>	Input Capacitance	V <sub>DS</sub> =-15V		954		
Coss	Output Capacitance	V <sub>GS</sub> =0V		115		pF
C <sub>RSS</sub>	Reverse Transfer Capacitance	f =1.0MHz		77		



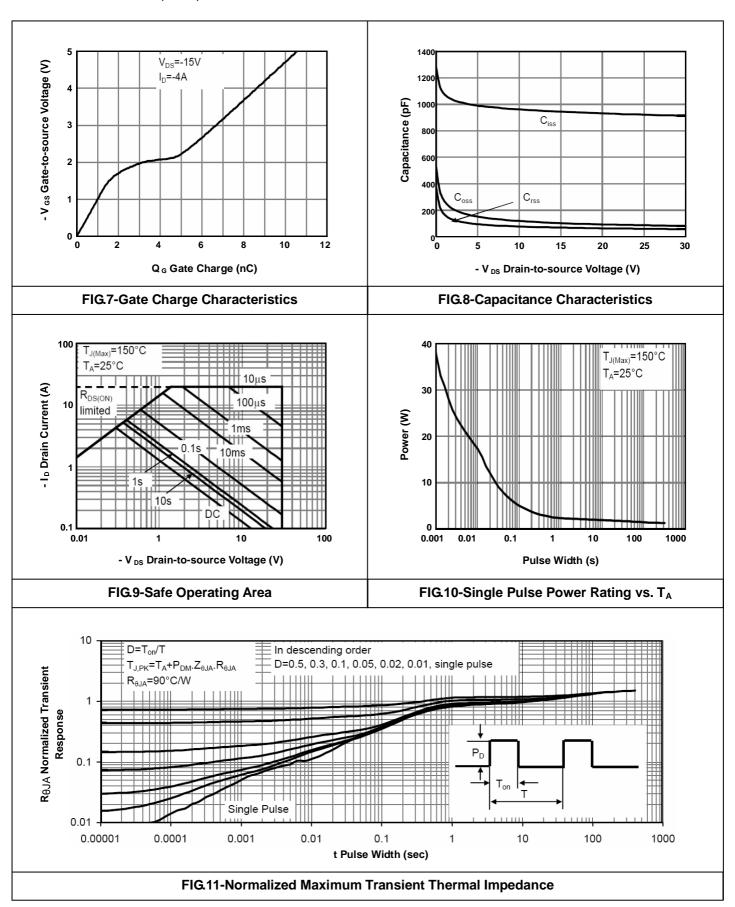
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### Typical Electrical Characteristics





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